

SMTY18AM

LOW FORWARD VOLTAGE TVS: Transky™

FEATURES AND BENEFITS

- High peak pulse power: 400W (8/20µs)
- Stand-off voltage 16V
- Low forward voltage: 0.48V @ 0.85A @ 25°C
- Low clamping factor V_{CL}/V_{BR}
- Fast response time
- Very thin package (1.0mm overall component height)

DESCRIPTION

The Transky[™] is designed specifically for portable equipments and miniaturized electronics devices subject to ESD transient overvoltages.

The Transky[™] combines the performance of a Transil[™] or TVS (Tansient Voltage Supressor) and low forward voltage Schottky diode in a monolithic structure.

COMPLIES WITH FOLLOWING STANDARDS

IEC 61000-4-2 Level 4:

15kV (Air discharge) 8kV (Contact discharge) MIL Standard 883E-Method 3015-7: class 3C Human Body Model (HBM)



Table 1: Order Code

Part Number	Marking
SMTY18AM	Y18



Symbol	Parameter	Value	Unit	
V _{PP}	IEC 61000-4-2 standard Air discharge Contact discharge		15 8	kV
P _{PP}	Peak pulse power dissipation (see note 1)	400	W	
I _{FSM}	Non repetitive surge peak forward current	T _p = 10 ms Tj = initial = Tamb	25	A
T _{stg}	Storage temperature range	-65 to + 175	°C	
Тj	Maximum operating junction temperature	150	°C	

Table 2: Absolute Ratings (limiting values)

Note 1: 8/20µs pulse waveform

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Table 3: Thermal Resistances

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient on PCB with recommended pad layout	250	°C/W

Table 4: Static Electrical Characteristics

 $(Tamb = 25^{\circ}C)$

Symbol	Parameter	
V_{BR}	Breakdown voltage	
I _{RM}	_eakage current @ V _{RM}	
V _{RM}	Stand-off voltage	
V _{CL}	Clamping voltage	
R _d	Dynamic impedance	
I _{PP}	Peak pulse current	
С	Capacitance	



I _{RM} max	I _{RM} max @ V _{RM} V _{CL} max @ I _{PP} V _F max @ 0.85A		α T max	C typ @ 0V		
Not	e 2	Note 3		Note 4		
mA	V	V	А	V	10 ⁻⁴ /°C	pF
4	16	20	1	0.48	8.8	500

Note 2: T_{amb} = 85°C Note 3: 8/20µs pulse waveform Note 4: Pulse test tp = 500µs, d< 2%

Figure 1: Peak pulse power versus exponential pulse duration



Figure 3: Average power dissipation versus ambient temperature



Figure 5: Thermal resistance junction to ambient versus copper surface under tab



Figure 2: Relative variation of peak pulse power versus initial junction temperature



Figure 4: Variation of thermal impedance junction to ambient versus pulse duration (Epoxy FR4, e_{cu} =35µm)



Figure 6: Reverse leakage current versus junction temperature (typical values)



Figure 7: Clamping voltage versus peak pulse current (typical values)





Figure 9: Forward voltage drop versus forward current (typical values)





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Figure 10: STmite Package Mechanical Data



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.85	1.00	1.15	0.033	0.039	0.045
A1	-0.05		0.05	-0.002		0.002
b	0.40		0.65	0.016		0.025
b2	0.70		1.00	0.027		0.039
С	0.10		0.25	0.004		0.010
D	1.75	1.90	2.05	0.069	0.007	0.081
E	1.75	1.90	2.05	0.069	0.007	0.081
Н	3.60	3.75	3.90	0.142	0.148	0.154
L	0.50	0.63	0.80	0.019	0.025	0.031
L2	1.20	1.35	1.50	0.047	0.053	0.059
L3		0.50			0.019	
		ref			ref	
R	0.07			0.003		
R1	0.07			0.003		

Figure 11: Foot Print Dimensions (in millimeters)



Table 5: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
SMTY18AM	Y18	STmite	15.5 mg	12000	Tape & reel

Table 6: Revision History

Date	Revision	Description of Changes
09-Jul-2004	1	First issue
13-Sep-2004	2	STmite package dimensions reference A1 change: from blank (min) to -0.05mm and from 0.10 (max) to 0.05mm.



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